

# AUTOMOTIVE CURRENT TRANSDUCER HC6F200-S





The HC6F family is for use on the electronic measurement of DC, AC or pulsed currents in high power and low voltage automotive applications with a galvanic isolation between the primary circuit (high power) and the secondary circuit (electronic circuit)

The HC6F family gives you the choice of having different current measuring ranges in the same housing.

### Features

- Open Loop transducer using the Hall effect
- Low voltage application
- Unipolar + 5 V DC power supply
- Primary current measuring range from 200 A up to 800 A
- Maximum rms primary admissible current: defined by busbar the magnetic core or the asic to have T° < + 150°C</li>
- Operating temperature range: 40°C < T° < + 125°C</li>
- Output voltage: full ratio-metric (in gain and offset)
- Compact design for PCB mounting.

## Advantages

- Excellent accuracy
- Very good linearity
- · Very low thermal offset drift
- Very low thermal gain drift
- Wide frequency bandwidth
- No insertion losses
- Very good ratio size/current range.

## Automotive applications

- Starter Generators
- Converters
- Inverters
- Drives.





## Principle of HC6F Family

The open loop transducers use an Hall effect integrated circuit.

The magnetic flux density B, contributing to the rise of the Hall voltage, is generated by the primary current  ${\bf I}_{\rm p}$  to be measured.

The current to be measured  $I_{p}$  is supplied by a current source i.e. battery or generator (Fig. 1).

Within the linear region of the hysteresis cycle, B is proportional to:

**B** 
$$(\mathbf{I}_{P})$$
 = constant (a) x  $\mathbf{I}_{P}$ 

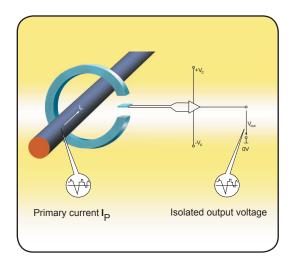
The Hall voltage is thus expressed by:

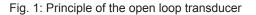
 $\mathbf{V}_{\mu}$ = (R<sub> $\mu$ </sub>/d) x I x constant (a) x I<sub>P</sub>

Except for  $\mathbf{I}_{\mathrm{p}},$  all terms of this equation are constant. Therefore:

$$\mathbf{V}_{\mu}$$
 = constant (b) x  $\mathbf{I}_{\mu}$ 

The measurement signal  $\mathbf{V}_{_{\rm H}}$  amplified to supply the user output voltage or current.



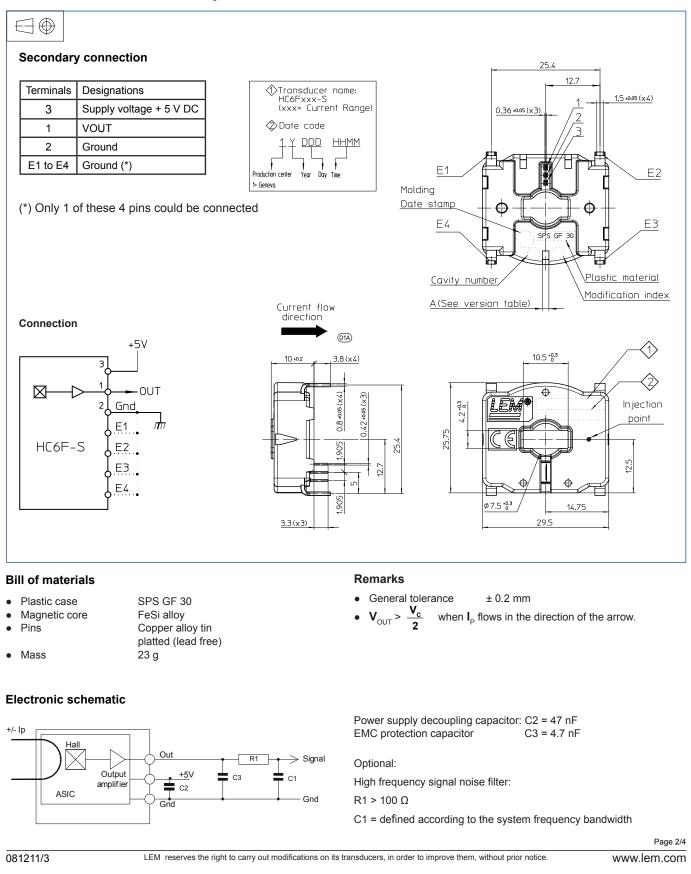


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# HC6F200-S

## Dimensions HC6F xxx-S family (in mm. 1mm = 0.0394 inch)





# HC6F200-S

## Absolute maximum ratings (not operating)

Parameter	Symbol	Unit	Specification	Conditions
Maximun peak primary current (not operating)	I <sub>P max</sub>	A	Defined by busbar to have $T^\circ \leq 150^\circ C$	
Primary nominal DC or current rms	I <sub>PN</sub>	A	Defined by busbar to have $T^\circ \leq 150^\circ C$	
Maximun supply voltage (not operating)	V <sub>C max</sub>	V	7	
Secondary maximum admissible power	P <sub>S max</sub>	mW	150	
Ambient operating temperature	T <sub>A</sub>	°C	- 40 < <b>T</b> <sub>A</sub> < 125°C	
Ambient storage temperature	T <sub>s</sub>	°C	- 40 < <b>T</b> <sub>s</sub> < 125°C	
Electrostatic discharge voltage	V <sub>ESD</sub>	V	2000	see page 4/4
Maximum admissible vibration	γ	m.s -2	100	see page 4/4
Rms voltage for AC isolation test 50 Hz, 1 min	V <sub>d</sub>	V	2000	
Reverse voltage <sup>1)</sup>	V <sub>c</sub>	V	0.5	1 min @ <b>T</b> <sub>A</sub> = 25°C

## **Operating characteristics**

	Question	L I with	Specification			Conditions			
	Symbol Un	Unit	Min	Typical	Max	Conditions			
Electrical Data									
Primary current, measuring range	I <sub>PM</sub>	А	-200	-	200	@ - 40°C < T° < 125°C			
Supply voltage 2)	V <sub>c</sub>	V	4.75	5	5.25	@ - 40°C < T° < 125°C			
Output voltage (Analog)	V <sub>OUT</sub>	V	$V_{OUT} = V_{C}/5 \times (2.5 + 0.01 \times I_{P})$		0.01 x I <sub>P</sub> )	@ - 40°C < T° < 125°C			
Sensitivity	G	V/A	0.0098	0.01	0.0102	@ <b>T</b> <sub>A</sub> = 25°C			
Offset voltage	Vo	V	2.463	2.5	2.537	@ $\mathbf{V}_{c} = 5 \text{ V}; \mathbf{T}_{A} = 25^{\circ}\text{C}; \mathbf{I}_{P} = 0 \text{ A}$			
Current consumption	I <sub>c</sub>	mA	-	15	20	@ - 40°C < T° < 125°C; 4.75 V < <b>V</b> <sub>c</sub> < 5.25 V			
Load resistance	R	KΩ	10	-	-				
Output internal resistance	<b>R</b> <sub>OUT</sub>	Ω	-	-	10				
Performance Data									
Sensitivity error	ε <sub>g</sub>	%	-2.0	±0.7	2.0	@ $T_{A} = 25^{\circ}C$ , $V_{C} = 5 V$ ; Gth = 0.01			
Electrical offset	I <sub>OE</sub>	А	-1.3	±0.5	1.3	@ <b>V</b> <sub>c</sub> = 5 V; <b>T</b> <sub>A</sub> = 25°C			
	V <sub>OE</sub>	mV	-13	±5	13				
Magnetic offset	I <sub>om</sub>	А	-2.4	±1.5	2.4	@ After excursion to $\pm I_p$ ; $T_A = 25^{\circ}C$			
	V <sub>OM</sub>	mV	-24	±15	24				
Temperature coefficient of	TCI <sub>OE</sub>	mA/°C	-14	8	+14	@ - 40°C < T° < 125°C; <b>V</b> <sub>c</sub> = 5 V			
	TCV	mV/°C	-0.14	±0.08	0.14				
Temperature coefficient of G	TCG	%/°C	-0.04	±0.02	0.04	@ - 40°C < T° < 125°C; <b>V</b> <sub>c</sub> = 5 V			
Linearity error	ε <sub>L</sub>	% I <sub>P</sub>	-1.0	±0.7	1.0	@ $I_{P}$ ; $V_{C}$ = 5 V, $T_{A}$ = 25°C			
Response time	t,	μs	-	8	15	@ di/dt = 50 A/µs; I <sub>T</sub> = 200 A			
Frequency bandwidth 3)	BW	kHz	20	-	-	@ -3 dB; I <sub>T</sub> = 40 A rms			
Output voltage noise peak-peak	V <sub>no p-p</sub>	mV	-	23	28	@ <b>T</b> <sub>A</sub> = 25°C; 0 Hz < f < 1 MHz			
Output voltage noise rms	V <sub>no rms</sub>	mV	-	2	3.5	@ <b>T</b> <sub>A</sub> = 25°C; 0 Hz < f < 1 MHz			

Notes: 1) Transducer not protected against reverse polarity

<sup>2)</sup> The output voltage  $V_{oUT}$  is fully ratio-metric and depends on the supply voltage  $V_c$ The  $V_c$  value must be measured and used with the following formula:

$$I_{\text{P}} = \left(V_{\text{out}} - \frac{V_{\text{c}}}{2}\right) \times \frac{1}{G} \times \frac{5}{V_{\text{c}}} \qquad \text{with } G \text{ in } (V \,/\, A)$$

<sup>3)</sup> Small signal only to avoid excessives heatings of the busbar, the magnetic core and the ASIC (< 150°C).

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## HC6F200-S PERFORMANCES PARAMETERS DEFINITIONS

#### Output noise voltage:

The output voltage noise is the result of the noise floor of the Hall elements and the linear  ${\rm I_c}$  amplifier gain.

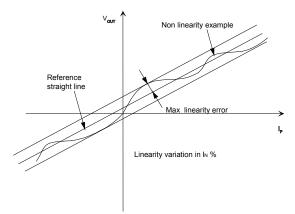
#### Magnetic offset:

The magnetic offset is the consequence of an over-current on the primary side. It's defined after an excursion of  ${\rm I}_{\rm P\,max^*}$ 

#### Linearity:

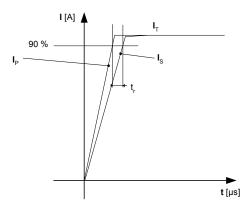
The maximum positive or negative discrepancy with a reference straight line  $V_{\text{OUT}}$  = f (I<sub>P</sub>).

Unit: linearity (%) expressed with full scale of I<sub>P max</sub>.



#### Response time (delay time) t,:

The time between the primary current signal and the output signal reach at 90 % of its final value



### **Typical:**

Theorical value or usual accuracy recorded during the production.

#### Sensitivity:

The Transducer's sensitivity **G** is the slope of the straight line  $V_{out} = f(I_p)$ , it must establish the relation:  $V_{out}(I_p) = V_c/5 (G \times I_p + 2.5) (*)$ 

(\*) For all symetrics transducers.

### Offset with temperature:

The error of the offset in the operating temperature is the variation of the offset in the temperature considered with the initial offset at  $25^{\circ}$ C.

The offset variation  $\mathbf{I}_{_{\mathrm{OT}}}$  is a maximum variation the offset in the temperature range:

 $I_{OT} = I_{OE} \max - I_{OE} \min$ 

The Offset drift  $\textbf{TCI}_{\text{OEAV}}$  is the  $\textbf{I}_{\text{OT}}$  value divided by the temperature range.

#### Sensitivity with temperature:

The error of the sensitivity in the operating temperature is the relative variation of sensitivity with the temperature considered with the initial offset at  $25^{\circ}$ C.

The sensitivity variation  $\mathbf{G}_{T}$  is the maximum variation (in ppm or %) of the sensitivity in the temperature range:

 $\mathbf{G}_{T} = (\text{Sensitivity max} - \text{Sensitivity min}) / \text{Sensitivity at } 25^{\circ}\text{C}.$ 

The sensitivity drift  $\textbf{TCG}_{\text{AV}}$  is the  $\textbf{G}_{\text{T}}$  value divided by the temperature range.

#### Offset voltage @ I<sub>p</sub> = 0 A:

Is the output voltage when the primary current is null. The ideal value of  $\mathbf{V}_{o}$  is  $\mathbf{V}_{c}/2$  at  $\mathbf{V}_{c} = 5$  V. So, the difference of  $\mathbf{V}_{o} - \mathbf{V}_{c}/2$  is called the total offset voltage error. This offset error can be attributed to the electrical offset (due to the resolution of the ASIC quiescent voltage trimming), the magnetic offset, the thermal drift and the thermal hysteresis.

#### **Environmental test specifications**

Name	Standard	Conditions				
Low T° storage	IEC 60068 Part 2-1	T° - 40°C / 100 H not connected				
Thermal shocks	IEC 60068 Part 2-14	T° - 30°C to 110°C /1000 cycles not connected				
Low T <sup>°</sup> operation at min supply voltage	IEC 60068 Part 2-1	T° - 40°C / 1000 H supply voltage = 4.75 V				
High T° operation at max supply voltage	IEC 60068 Part 2-2	T° 125°C / 1000 H supply voltage = 5.25 V				
Temperature humidity bias	IEC 60068 Part 2-3	T° 90°C / 95 % RH/ 1000 H supp voltage = 5.25 V				
Mechanical Tests						
Vibration	IEC 60068 Part 2-64	Room T°, acceleration 100 m/s2, frequency 20 to 500 Hz/96 H each axis				
Drop test	IEC 60068 Part 2-29	Height 750 mm concrete floor each directions				
EMC Test						
Electrostatic discharge	JESD22-A114-B	Applied voltage = ± 2 kV pin to pin number of discharge = 1				

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